708 616.
708 628.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

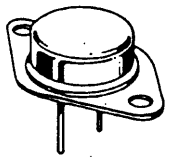
NPN MJ15001 PNP MJ15002

COMPLEMENTARY SILICON POWER TRANSISTORS

The MJ15001 and MJ15002 are EpiBase power transistors designed for high power audio, disk head positioners and other linear applications.

- High Safe Operating Area (100% Tested) —
  200 W @ 40 V
  50 W @ 100 V
- For Low Distortion Complementary Designs
- High DC Current Gain —
  h_{FE} = 25 (Min) @ I_C = 4 Adc

15 AMPERE
POWER TRANSISTORS
COMPLEMENTARY SILICON
140 VOLTS
200 WATTS

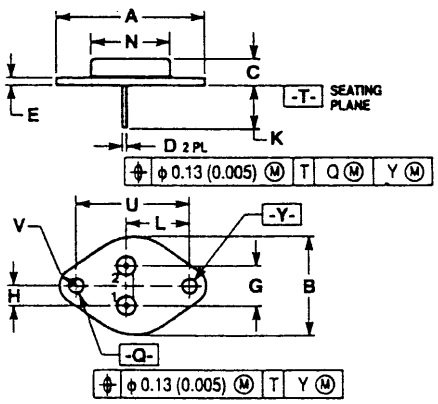


MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	140	Vdc
Collector-Base Voltage	V_{CBO}	140	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Collector Current — Continuous	I_C	15	Adc
Base Current — Continuous	I_B	5	Adc
Emitter Current — Continuous	I_E	20	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	200 1.14	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.875	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/16" from Case for ≤10s.	T_L	265	°C



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.
4. 001-05 AND -06 OBSOLETE, NEW STANDARD 001-07.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	39.37 REF		1.550 REF	
B	—	26.67	—	1.050
C	6.35	8.51	0.250	0.335
D	0.97	1.09	0.038	0.043
E	1.40	1.77	0.055	0.070
G	10.92 BSC		0.430 BSC	
H	5.46 BSC		0.215 BSC	
K	11.18	12.19	0.440	0.480
L	16.89 BSC		0.665 BSC	
N	—	21.08	—	0.830
Q	3.84	4.19	0.151	0.165
U	30.15 BSC		1.187 BSC	
V	3.33	4.77	0.131	0.188

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

CASE 1-07
TO-204AA
(TO-3)

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (1) (I_C = 200 mAdc, I_B = 0)	$V_{CEO(sus)}$	140	–	Vdc
Collector Cutoff Current (V_{CE} = 140 Vdc, $V_{BE(off)}$ = 1.5 Vdc)	I_{CEX}	–	100	μAdc
(V_{CE} = 140 Vdc, $V_{BE(off)}$ = 1.5 Vdc, T_C = 150°C)			2	mAdc
Collector Cutoff Current (V_{CE} = 140 Vdc, I_B = 0)	I_{CEO}	–	250	μAdc
Emitter Cutoff Current (V_{EB} = 5 Vdc, I_C = 0)	I_{EBO}	–	100	μAdc
SECOND BREAKDOWN				
Second Breakdown Collector Current with Base Forward Biased (V_{CE} = 40 Vdc, t = 1 s (non-repetitive))	$I_{S/b}$	5	–	Adc
(V_{CE} = 100 Vdc, t = 1 s (non-repetitive))		0.5	–	
ON CHARACTERISTICS				
DC Current Gain (I_C = 4 Adc, V_{CE} = 2 Vdc)	h_{FE}	25	150	–
Collector-Emitter Saturation Voltage (I_C = 4 Adc, I_B = 0.4 Adc)	$V_{CE(sat)}$	–	1	Vdc
Base-Emitter On Voltage (I_C = 4 Adc, V_{CE} = 2 Vdc)	$V_{BE(on)}$	–	2	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain – Bandwidth Product (I_C = 0.5 Adc, V_{CE} = 10 Vdc, f_{test} = 0.5 MHz)	f_T	2	–	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f_{test} = 1 MHz)	C_{ob}	–	1000	pF

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

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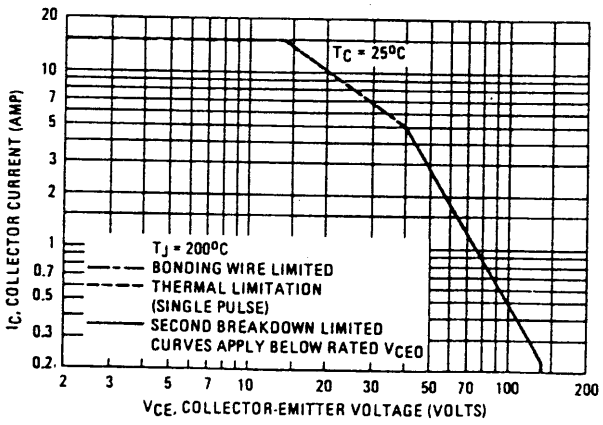
FIGURE 1 – ACTIVE-REGION SAFE OPERATING AREA



There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)}$ = 200°C; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

TYPICAL CHARACTERISTICS

FIGURE 2 – CAPACITANCES

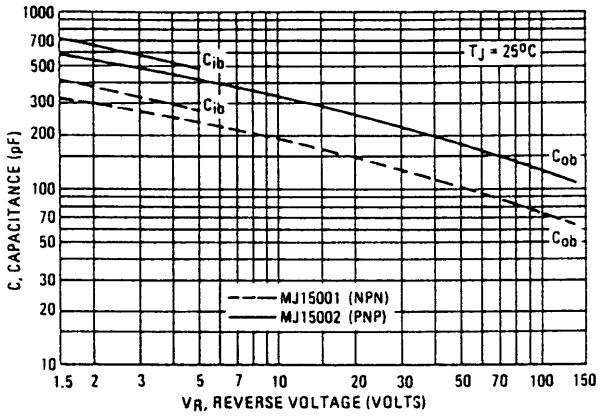


FIGURE 3 – CURRENT-GAIN – BANDWIDTH PRODUCT

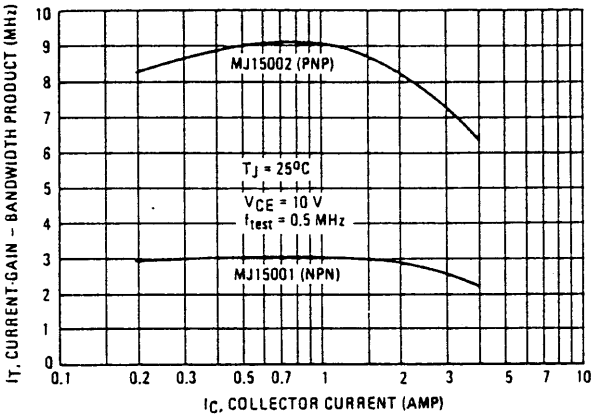
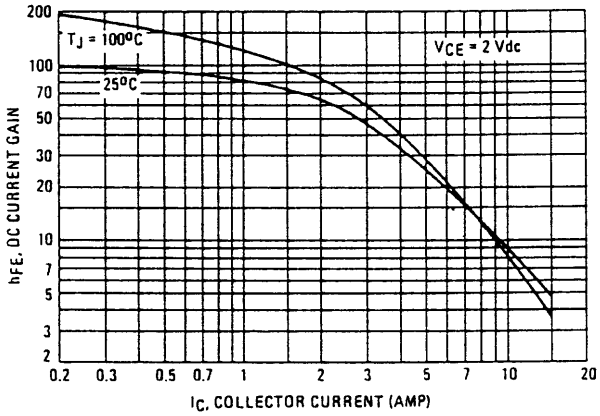


FIGURE 4 – DC CURRENT GAIN

MJ15001



MJ15002

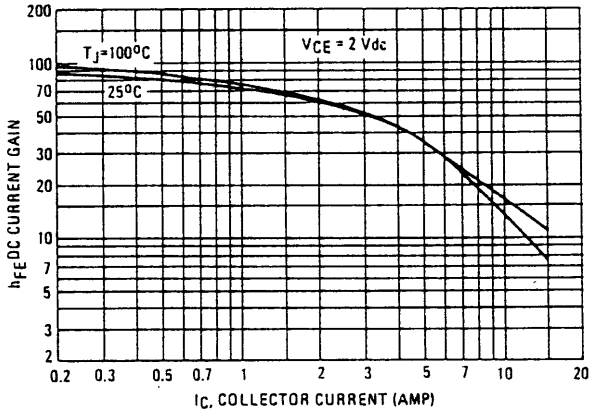
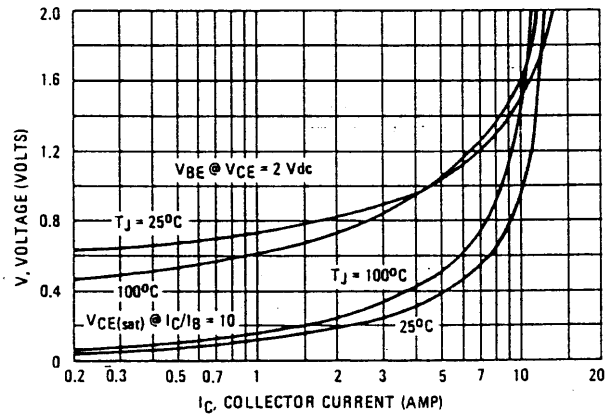
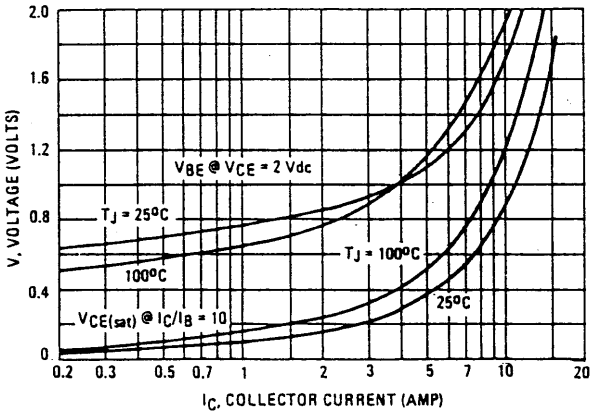


FIGURE 5 – "ON" VOLTAGE

MJ15001



MJ15002



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